

SANYO Semiconductors DATA SHEET

P-Channel Silicon MOSFET

ECH8306— General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	٧
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-12	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-100V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-1A	2.9	4.9		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-1A, V _G S=-10V		170	225	mΩ
	R _{DS} (on)2	I _D =-0.5A, V _G S=-4V		195	275	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		1600		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		85		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		72		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		13.5		ns
Rise Time	t _r	See specified Test Circuit.		10		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		190		ns
Fall Time	tf	See specified Test Circuit.		54		ns
Total Gate Charge	Qg	V _{DS} =-50V, V _{GS} =-10V, I _D =-2A		33		nC
Gate-to-Source Charge	Qgs	V _{DS} =-50V, V _{GS} =-10V, I _D =-2A		3.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-50V, V _{GS} =-10V, I _D =-2A		6.0		nC
Diode Forward Voltage	V _{SD}	I _S =-2A, V _G S=0V		-0.8	-1.2	V

Marking : JH

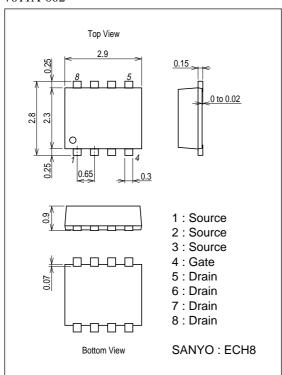
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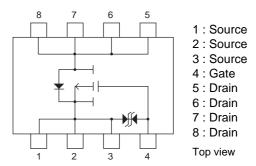
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Package Dimensions

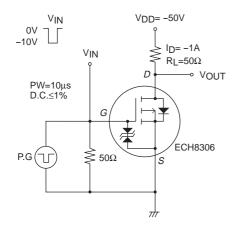
unit : mm 7011A-002

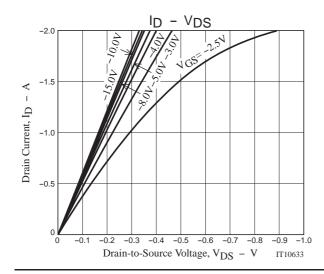


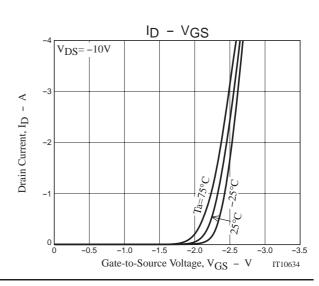
Electrical Connection



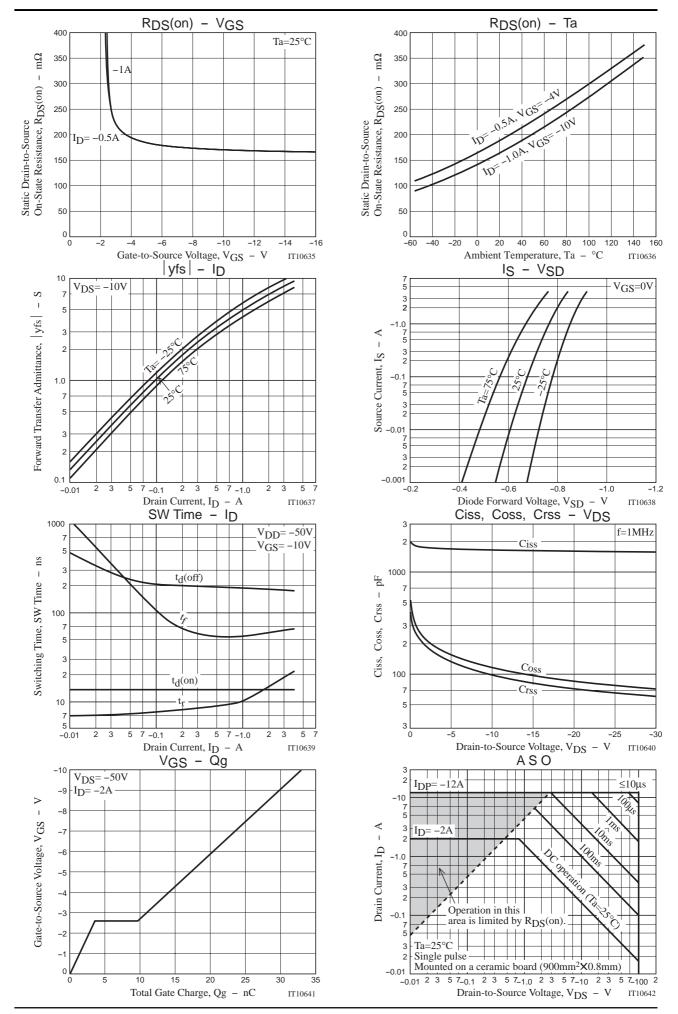
Switching Time Test Circuit



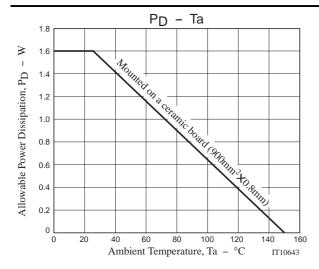




ECH8306



ECH8306



Note on usage: Since the ECH8306 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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